

# GaAs SPDT Switch DC - 3.0 GHz

Rev. V6

### **Features**

- Low Cost Plastic: SC-70 (SOT-363) Package
- Low Insertion Loss: < 0.3 dB @ 900 MHz
- Low Power Consumption: < 15 μA @ -2.3 Volts
- Positive or Negative 2.3 to 8 Volt Control

## **Description**

M/A-COM's SW-456 is a GaAs monolithic switch in a low cost SC-70 (SOT-363) surface mount plastic The SW-456 is ideally suited for package. applications where very low power consumption, low insertion loss, very small size and low cost are Typical applications are in dual band systems where switching between small signal components is required, i.e. filter banks, single-band LNA's, converters, etc. The SW-456 can be used in applications up to 0.25 watts in systems such as cellular, PCS, DCS1800, GSM, CDMA. W-CDMA and other analog/digital wireless communication systems.

The SW-456 is fabricated using a mature 0.5 micron PHEMT process. The process features full passivation for performance and reliability.

# Ordering Information <sup>1</sup>

Part Number	Package		
SW-456 PIN	Bulk Packaging		
SW-456TR	1000 piece reel		
SW-456TR-3000	3000 piece reel		
SW-456SMB	Sample Test Board		

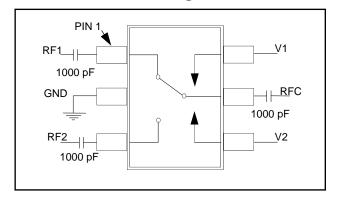
<sup>1.</sup> Reference Application Note M513 for reel size information.

# Absolute Maximum Ratings <sup>2</sup>

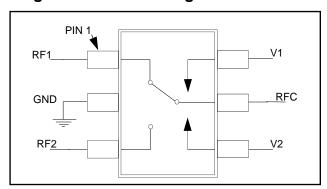
Parameter	Absolute Maximum
Input Power (0.5 - 3.0 GHz) 3 V Control 5 V Control	+30 dBm +33 dBm
Operating Voltage	+8.5 volts
Operating Temperature	-40°C to +85°C
Storage Temperature	-65°C to +150°C

<sup>2.</sup> Exceeding any one or combination of these limits may cause permanent damage to this device.

# Functional Schematic Positive Control Voltage



# Functional Schematic Negative Control Voltage



## **Pin Configuration**

PIN	Function	Description		
1	RF1	RF In/Out		
2	GND	RF Ground		
3	RF2	RF In/Out		
4	V2	V <sub>CTRL2</sub>		
5	RFC	RF Common		
6	V1	$V_{CTRL1}$		



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# Electrical Specifications: $T_A = 25^{\circ}C$ , $V_{CTL} = 0$ , -2.3 volts (unless otherwise specified)<sup>3</sup>

Parameter	Test Conditions Unit		Min.	Тур.	Max.
Insertion Loss <sup>4</sup>	DC - 1 GHz 1 - 2 GHz 2 - 3 GHz	dB dB dB		0.35 0.45 0.56	0.5 0.6 0.8
Isolation	DC - 1 GHz dB 1 - 2 GHz dB 2 - 3 GHz dB		20 15 10	22 17 12	_ _ _
$V_{\sf SWR}$	DC - 3 GHz	Ratio	_	1.2:1	1.4:1
P <sub>1dB</sub> (2.3V supply)	500 MHz - 3 GHz	dBm	_	21	_
P <sub>1dB</sub> (3V supply)	500 MHz - 3 GHz	dBm	_	27	_
Input IP <sub>2</sub>	2-Tone 900 MHz, 5 MHz spacing (3.0 V)	2-Tone 900 MHz, 5 MHz spacing (3.0 V) dBm		81	_
Input IP <sub>3</sub>	2-Tone 900 MHz, 5 MHz spacing (3.0 V)	dBm	_	52	_
Trise, Tfall	10% to 90% RF, 90% to 10% RF	ns	_	25	_
Ton, Toff	50% Control to 90% RF, Control to 10% RF	ns	_	25	_
Transients	In-Band	mV	_	25	_
Control Current	V <sub>CTL</sub> = -2.3 V μA —		_	4	15

<sup>3.</sup> External DC blocking capacitors are required on all RF ports when using positive voltage control.

#### Qualification

Qualified to M/A-COM specification REL-201, Process Flow -2.

## **Handling Procedures**

Please observe the following precautions to avoid damage:

## **Static Sensitivity**

Gallium Arsenide Integrated Circuits are sensitive to electrostatic discharge (ESD) and can be damaged by static electricity. Proper ESD control techniques should be used when handling these devices.

### **Truth Table**

Mode (Control)	V1	V2	RFC - RF1	RFC - RF2
Positive <sup>5</sup>	0 ± 0.2 V	+2.3 to +8 V	Off	On
	+2.3 to +8 V	0 ± 0.2 V	On	Off
Negative <sup>6</sup>	0 ± 0.2 V	-2.3 V to -8 V	On	Off
	-2.3 V to -8 V	0 ± 0.2 V	Off	On

- 5. External DC blocking capacitors are required on all RF ports. 1000 pF capacitors used for positive control voltage. For higher frequency operation, smaller value DC blocking capacitors can be substituted.
- 6. If negative control is used, DC blocking capacitors are not required on RF ports.

Solutions has under development. Performance is based on engineering tests. Specifications are typical. Mechanical outline has been fixed. Engineering samples and/or test data may be available. Commitment to produce in volume is not guaranteed.

<sup>4.</sup> Insertion loss can be optimized by varying the DC blocking capacitor value, e.g. 1000 pF for 100 MHz - 1 GHz, 39 pF for 0.5 - 3 GHz.

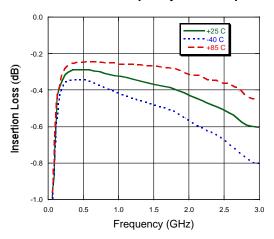


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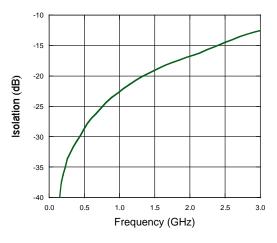
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## **Typical Performance Curves**

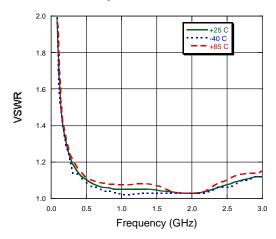
### Insertion Loss vs. Frequency Over Temperature



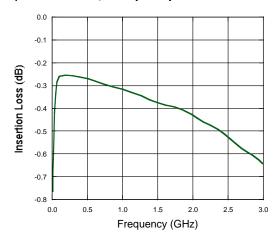
### Isolation vs. Frequency Over Temperature



#### VSWR Over Temperature



### Insertion Loss vs. Frequency (+2.3 V Control, 1000 pF Capacitor on RF Ports)



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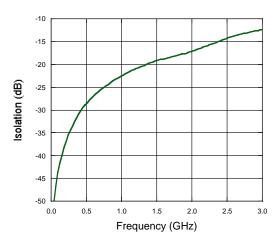


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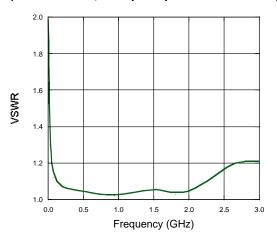
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## **Typical Performance Curves**

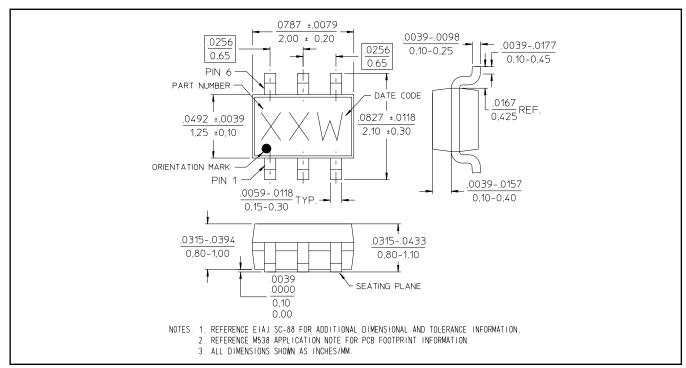
Isolation vs. Frequency (+2.3 V Control, 1000 pF Capacitor on RF Ports)



#### VSWR vs. Frequency (+2.3 V Control, 1000 pF Capacitor on RF Ports)



# SC-70 (SOT-363)



<sup>•</sup> India Tel: +91.80.43537383 Visit www.macomtech.com for additional data sheets and product information.

<sup>•</sup> China Tel: +86.21.2407.1588